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PPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/045,895 10/29/2001		Stephen Keetai Park	2000.029996/TT3586C	3826	
23720	7590 05 02 2003				
WILLIAMS, MORGAN & AMERSON, P.C. 10333 RICHMOND, SUITE 1100 HOUSTON, TX 77042			EXAMINER		
			LEE, HSIEN MING		
			ART UNIT	PAPER NUMBER	
			2823	0	
			DATE MAILED: 05/02/2003	٥	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	•	Application No.		Applicant(s)		-/	
		10/045,895		PARK, STEPHEN	KEETAI		
•	Office Action Summary	Examiner	,	Art Unit			
		Hsien-Ming Lee		2823	Idroop		
Period fo	The MAILING DATE of this communication ap r Reply	pears on the cover sne	et with the coi	rresponderice ad	aress		
THE N - Exter - after - If the - If NO - Failur - Any r	DRTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. Issues of time may be available under the provisions of 37 CFR 1 SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days. a reppend for reply is specified above, the maximum statutory period to to eply within the set or extended period for reply will, by statut eply received by the Office later than three months after the mailing dipatent term adjustment. See 37 CFR 1.704(b)	136(a) In no event, however, r ly within the statutory minimum will apply and will expire SIX (6 e. cause the application to become	may a reply be timel of thirty (30) days v i) MONTHS from the ome ABANDONED	y filed will be considered timel e mailing date of this c (35 U S C § 133).	y ommunication.		
1)	Responsive to communication(s) filed on	 ·					
2a)	This action is FINAL . 2b)⊠ T	his action is non-final.					
3) Dispositi	Since this application is in condition for allow closed in accordance with the practice under on of Claims	ance except for forma Ex parte Quayle, 193	al matters, pro 35 C.D. 11, 45	secution as to th 3 O.G. 213.	ne merits is		
4)🖂	Claim(s) 1-20,41 and 42 is/are pending in the	application.					
	4a) Of the above claim(s) is/are withdra	wn from consideration	n.				
5)	Claim(s) is/are allowed.						
6)⊠	Claim(s) 1-20,41 and 42 is/are rejected.						
7)🖂	Claim(s) 6, 11, 16 is/are objected to.						
	Claim(s) are subject to restriction and/	or election requiremen	nt.				
	on Papers						
	The specification is objected to by the Examina		1 - L:4 - W 4 - D:	the Everniner			
10)⊠	The drawing(s) filed on 29 October 2001 is/are						
44)	Applicant may not request that any objection to the proposed drawing correction filed on						
11)	If approved, corrected drawings are required in re			ed by the Exami			
12)	The oath or declaration is objected to by the E						
	under 35 U.S.C. §§ 119 and 120	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,					
1	Acknowledgment is made of a claim for foreig	n priority under 35 U	S.C. § 119(a)-	-(d) or (f).			
	☐ All b)☐ Some * c)☐ None of:	in priority arraor of or	0.0.3(=)	(-, (-,-			
a)		its have been received	1				
	 Certified copies of the priority documents have been received. Certified copies of the priority documents have been received in Application No 						
* 5	Copies of the certified copies of the price application from the International Bee the attached detailed Office action for a list.	ority documents have ureau (PCT Rule 17.2	been received (a)).	in this National	Stage		
	Acknowledgment is made of a claim for domes				I application)		
а) The translation of the foreign language packnowledgment is made of a claim for domes	rovisional application h	nas been rece	ived.			
Attachmen				(OTO 440) 5	- (-)		
2) Notice	te of References Cited (PTO-892) te of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Not	tice of Informal Pa	(PTO-413) Paper No atent Application (P1			
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DETAILED ACTION

Specification

1. The disclosure is objected to because of the following informalities: the "CROSS RELATED APPLICATION DATA" is not complete, i.e. "...09/493,384, filed January 28, 2000, now U.S. Patent No. _____ "should be -- 09/493,384, filed January 28, 2000, now U.S. Patent No. 6,355,555 --. Appropriate correction is required.

Claim Objections

2. Claims 6, 11 and 16 are objected to because of the following informalities: in-consistent terminology, i.e. "a structure layer" (claim 11, line 2) versus "the structure" (claim 11, line 16).

Claim 6, at line 4 and claim 16, at line 4, "high dielectric constant (high K), where K" should be -- high dielectric constant (high K) material, wherein K--. Appropriate correction is required.

Claim Rejections - 35 USC § 112

- The following is a quotation of the second paragraph of 35 U.S.C. 112:
 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 4. Claims 1 and 7 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1. at line 6, "forming an opening in the sacrificial dielectric layer" renders indefinite because it is unclear whether "the sacrificial dielectric layer" refers to "first sacrificial dielectric layer" or "second sacrificial dielectric layer." The same problem also appears in claim 7. line 4.

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Double Patenting

5. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

- 6. Claims 1-22 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-20 of U.S. Patent No. 6,355,555 in view of Boeck et al. (US 5,880,018).
- U.S. Patent No. 6,355,555 claims a <u>common subject matter</u> as claimed, i.e. the subject mater as recited in claims 1-20 of the Patent are equivalent to that of claims 1-20 of the present application. The Patent does not claim forming the fist sacrificial dielectric layer *adjacent a contact, i.e. an intermetal via connect.*

Boeck et al. in an analogous art teach a method comprising: (a) forming a sacrificial dielectric layer 18 above a structure layer 16/12 and *adjacent to a contact, i.e. the copper intermetal via connect 14/20 (Fig.1)*;(b) forming an opening in the sacrificial dielectric layer 18:(c) forming at least one barrier metal layer (Ta; see col. 4. lines 20-28) above the sacrificial dielectric layer 18 and in the opening; (d) depositing copper layer above the at least one barrier metal layer (Ta) in the opening; (e) forming the copper interconnect by removing the copper layer and the at least one barrier metal layer above the sacrificial dielectric layer 18 by CMP

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technique, leaving the copper interconnect 20 in the opening (Fig. 3); (f) removing the sacrificial dielectric layers 18 above the structure layer and adjacent the copper interconnect (Fig. 4); and (g) forming a low dielectric constant dielectric layer 22 by chemical vapor deposition above the structure layer and adjacent the copper interconnect (Fig. 5).

Therefore, it would have been obvious to one of the ordinary skill in the art, at the time the invention was made, to form the first sacrificial dielectric layer adjacent to the contact as taught by Boeck and further proceed to the subsequent processing steps of the Patent since by this manner it would provide a satisfactory method for forming copper interconnect structure.

Conclusion

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Besser et al. to US 2001/0051420 teach some claimed steps as illustrated in Figs.1-7.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hsien-Ming Lee whose telephone number is 703-305-7341. The examiner can normally be reached on M-F (9:00 \sim 5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

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Hsien-Ming Lee Examiner Art Unit 2823

April 28, 2003

WILLIAM DIVIN COLLMAN

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